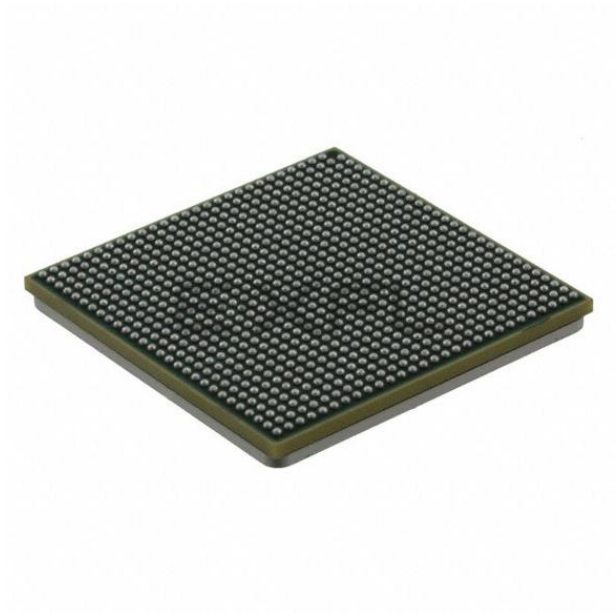

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.0GHz
Co-Processors/DSP	Signal Processing; SPE, Security; SEC
RAM Controllers	DDR, DDR2, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmpc8544eavtaqg

  - General-purpose chip select machine (GPCM)
  - Three user programmable machines (UPMs)
- Parity support
- Default boot ROM chip select with configurable bus width (8, 16, or 32 bits)

- Two enhanced three-speed Ethernet controllers (eTSECs)
  - Three-speed support (10/100/1000 Mbps)
  - Two IEEE Std 802.3™, IEEE 802.3u, IEEE 802.3x, IEEE 802.3z, IEEE 802.3ac, and IEEE 802.3ab-compliant controllers
  - Support for various Ethernet physical interfaces:
    - 1000 Mbps full-duplex IEEE 802.3 GMII, IEEE 802.3z TBI, RTBI, SGMII, and RGMII.
    - 10/100 Mbps full- and half-duplex IEEE 802.3 MII, IEEE 802.3 RGMII, and RMII.
  - Flexible configuration for multiple PHY interface configurations.
  - TCP/IP acceleration and QoS features available
    - IP v4 and IP v6 header recognition on receive
    - IP v4 header checksum verification and generation
    - TCP and UDP checksum verification and generation
    - Per-packet configurable acceleration
    - Recognition of VLAN, stacked (queue in queue) VLAN, 802.2, PPPoE session, MPLS stacks, and ESP/AH IP-security headers
    - Supported in all FIFO modes
  - Quality of service support:
    - Transmission from up to eight physical queues
    - Reception to up to eight physical queues
  - Full- and half-duplex Ethernet support (1000 Mbps supports only full duplex):
    - IEEE 802.3 full-duplex flow control (automatic PAUSE frame generation or software-programmed PAUSE frame generation and recognition)
  - Programmable maximum frame length supports jumbo frames (up to 9.6 Kbytes) and IEEE Std 802.1™ virtual local area network (VLAN) tags and priority
  - VLAN insertion and deletion
    - Per-frame VLAN control word or default VLAN for each eTSEC
    - Extracted VLAN control word passed to software separately
  - Retransmission following a collision
  - CRC generation and verification of inbound/outbound frames
  - Programmable Ethernet preamble insertion and extraction of up to 7 bytes
  - MAC address recognition:
    - Exact match on primary and virtual 48-bit unicast addresses
    - VRRP and HSRP support for seamless router fail-over
    - Up to 16 exact-match MAC addresses supported

Table 1. Absolute Maximum Ratings[1] (continued)

Characteristic		Symbol	Max Value	Unit	Notes
DDR and DDR2 DRAM I/O voltage		GV_{DD}	–0.3 to 2.75 –0.3 to 1.98	V	—
Three-speed Ethernet I/O, MII management voltage		LV_{DD} (eTSEC1)	–0.3 to 3.63 –0.3 to 2.75	V	—
		TV_{DD} (eTSEC3)	–0.3 to 3.63 –0.3 to 2.75	V	—
PCI, DUART, system control and power management, I^2C, and JTAG I/O voltage		OV_{DD}	–0.3 to 3.63	V	—
Local bus I/O voltage		BV_{DD}	–0.3 to 3.63 –0.3 to 2.75 –0.3 to 1.98	V	—
Input voltage	DDR/DDR2 DRAM signals	MV_{IN}	–0.3 to (GV_{DD} + 0.3)	V	2
	DDR/DDR2 DRAM reference	MV_{REF}	–0.3 to (GV_{DD} + 0.3)	V	2
	Three-speed Ethernet signals	LV_{IN} TV_{IN}	–0.3 to (LV_{DD} + 0.3) –0.3 to (TV_{DD} + 0.3)	V	2
	Local bus signals	BV_{IN}	–0.3 to (BV_{DD} + 0.3)	V	—
	DUART, SYSCLK, system control and power management, I^2C, and JTAG signals	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	2
	PCI	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	2
Storage temperature range		T_{STG}	–55 to 150	°C	—

Notes:
1. Functional and tested operating conditions are given in Table 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause.
2. (M,L,O)V_{IN}, and MV_{REF} may overshoot/undershoot to a voltage and for a maximum duration as shown in Figure 2.

2.1.2 Recommended Operating Conditions

Table 2 provides the recommended operating conditions for this device. Note that the values in Table 2 are the recommended and tested operating conditions. Proper device operation outside these conditions is not guaranteed.

Table 2. Recommended Operating Conditions

Characteristic	Symbol	Recommended Value	Unit	Notes
Core supply voltage	V_{DD}	1.0 ± 50 mV	V	—
PLL supply voltage	AV_{DD}	1.0 ± 50 mV	V	1
Core power supply for SerDes transceivers	SV_{DD}	1.0 ± 50 mV	V	—
Pad power supply for SerDes transceivers	XV_{DD}	1.0 ± 50 mV	V	—
DDR and DDR2 DRAM I/O voltage	GV_{DD}	2.5 V ± 125 mV 1.8 V ± 90 mV	V	2

Table 12. DDR SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 2.5 V (continued)

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Output low current (V_{OUT} = 0.42 V)	I_{OL}	16.2	—	mA	—

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REF} is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail should track variations in the DC level of MV_{REF}.

Table 13 provides the DDR I/O capacitance when GV_{DD}(typ) = 2.5 V.

Table 13. DDR SDRAM Capacitance for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. GV_{DD} = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.

Table 14 provides the current draw characteristics for MV_{REF}.

Table 14. Current Draw Characteristics for MV_{REF}

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Current draw for MV_{REF}	I_{MVREF}	—	500	μA	1

Note:
1. The voltage regulator for MV_{REF} must be able to supply up to 500 μA current.

6.2 DDR SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR SDRAM interface.

6.2.1 DDR SDRAM Input AC Timing Specifications

Table 15 provides the input AC timing specifications for the DDR SDRAM when GV_{DD}(typ) = 1.8 V.

Table 15. DDR2 SDRAM Input AC Timing Specifications for 1.8-V Interface

At recommended operating conditions.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	MV_{REF} – 0.25	V	—
AC input high voltage	V_{IH}	MV_{REF} + 0.25	—	V	—

Table 18. DDR SDRAM Output AC Timing Specifications (continued)

At recommended operating conditions.

Parameter	Symbol[1]	Min	Max	Unit	Notes
MDQS postamble	t_{DDKHME}	0.4 x tMCK	0.6 x tMCK	ns	6

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
2. All MCK/$\overline{\text{MCK}}$ referenced measurements are made from the crossing of the two signals ±0.1 V.
3. ADDR/CMD includes all DDR SDRAM output signals except MCK/$\overline{\text{MCK}}$, $\overline{\text{MCS}}$, and MDQ/MECC/MDM/MDQS.
4. Note that t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK[n] clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register. This will typically be set to the same delay as the clock adjust in the CLK_CNTL register. The timing parameters listed in the table assume that these two parameters have been set to the same adjustment value. See the *MPC8544E PowerQUICC III Integrated Communications Processor Reference Manual,* for a description and understanding of the timing modifications enabled by use of these bits.
5. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the microprocessor.
6. All outputs are referenced to the rising edge of MCK[n] at the pins of the microprocessor. Note that t_{DDKHMP} follows the symbol conventions described in note 1.
7. Maximum DDR1 frequency is 400 MHz.

NOTE

For the ADDR/CMD setup and hold specifications in Table 18, it is assumed that the clock control register is set to adjust the memory clocks by ½ applied cycle.

Figure 4 shows the DDR SDRAM output timing for the MCK to MDQS skew measurement (t_{DDKHMH}).

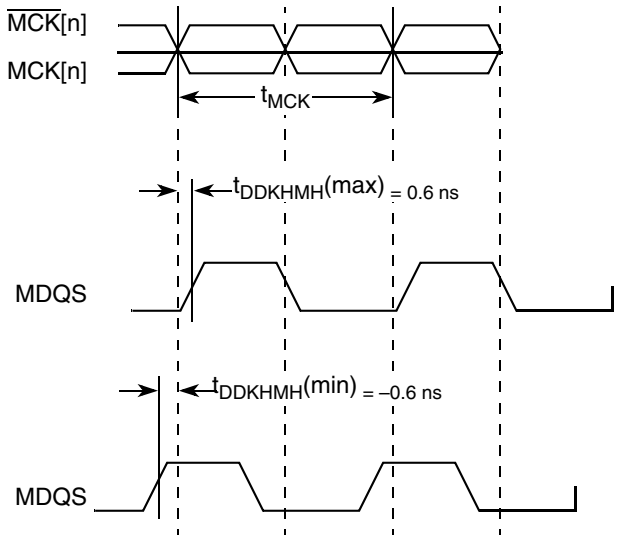

Figure 4. Timing Diagram for t_{DDKHMH}

8.6.1 MII Transmit AC Timing Specifications

Table 32 provides the MII transmit AC timing specifications.

Table 32. MII Transmit AC Timing Specifications

At recommended operating conditions with L/TV_{DD} of 3.3 V ± 5% or 2.5 V ± 5%

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit	Notes
TX_CLK clock period 10 Mbps	t_{MTX}	—	400	—	ns	—
TX_CLK clock period 100 Mbps	t_{MTX}	—	40	—	ns	—
TX_CLK duty cycle	t_{MTXH}/t_{MTX}	35	—	65	%	—
TX_CLK to MII data TXD[3:0], TX_ER, TX_EN delay	t_{MTKHDX}	1	5	15	ns	—
TX_CLK data clock rise (20%–80%)	t_{MTXR}	1.0	—	4.0	ns	—
TX_CLK data clock fall (80%–20%)	t_{MTXF}	1.0	—	4.0	ns	—

Note:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MTKHDX} symbolizes MII transmit timing (MT) for the time t_{MTX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{MTX} represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 16 shows the MII transmit AC timing diagram.

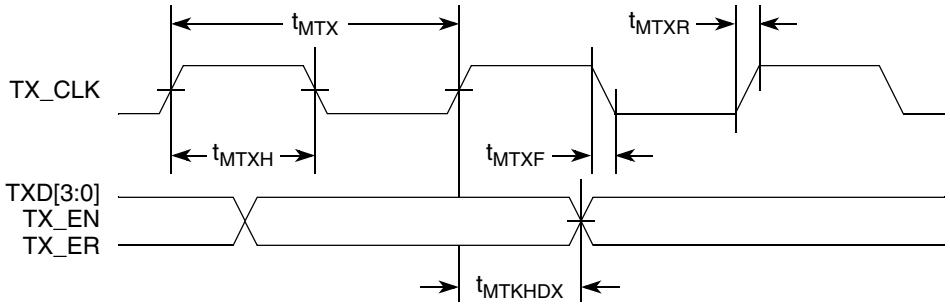

Figure 16. MII Transmit AC Timing Diagram

8.6.2 MII Receive AC Timing Specifications

Table 33 provides the MII receive AC timing specifications.

Table 33. MII Receive AC Timing Specifications

At recommended operating conditions with L/TVDD of 3.3 V ± 5%.or 2.5 V ± 5%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit	Notes
RX_CLK clock period 10 Mbps	t_{MRX}	—	400	—	ns	—
RX_CLK clock period 100 Mbps	t_{MRX}	—	40	—	ns	—
RX_CLK duty cycle	t_{MRXH}/t_{MRX}	35	—	65	%	—

Table 46. Local Bus General Timing Parameters (BV_{DD} = 2.5 V)—PLL Enabled (continued)

Parameter	Symbol[1]	Min	Max	Unit	Notes
Local bus clock to output high impedance for LAD/LDP	$t_{LBKHOZ2}$	—	2.6	ns	5

Notes:
1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(First two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to LSYNC_IN for PLL enabled and internal local bus clock for PLL bypass mode.
3. All signals are measured from $BV_{DD}/2$ of the rising edge of LSYNC_IN for PLL enabled or internal local bus clock for PLL bypass mode to $0.4 \times BV_{DD}$ of the signal in question for 2.5-V signaling levels.
4. Input timings are measured at the pin.
5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
6. t_{LBOTOT} is a measurement of the minimum time between the negation of LALE and any change in LAD. t_{LBOTOT} is programmed with the LBCR[AHD] parameter.
7. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at $BV_{DD}/2$.

Table 47 describes the general timing parameters of the local bus interface at BV_{DD} = 1.8 V DC.

Table 47. Local Bus General Timing Parameters (BV_{DD} = 1.8 V DC)

Parameter	Symbol[1]	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	7.5	12	ns	2
Local bus duty cycle	t_{LBKH}/t_{LBK}	43	57	%	—
LCLK[n] skew to LCLK[m] or LSYNC_OUT	$t_{LBKSKEW}$	—	150	ps	7
Input setup to local bus clock (except LUPWAIT)	$t_{LBIVKH1}$	2.6	—	ns	3, 4
LUPWAIT input setup to local bus clock	$t_{LBIVKH2}$	1.9	—	ns	3, 4
Input hold from local bus clock (except LUPWAIT)	$t_{LBIXKH1}$	1.1	—	ns	3, 4
LUPWAIT input hold from local bus clock	$t_{LBIXKH2}$	1.1	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH setup and hold time)	t_{LBOTOT}	1.2	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	$t_{LBKHOV1}$	—	3.2	ns	—
Local bus clock to data valid for LAD/LDP	$t_{LBKHOV2}$	—	3.2	ns	3
Local bus clock to address valid for LAD	$t_{LBKHOV3}$	—	3.2	ns	3
Local bus clock to LALE assertion	$t_{LBKHOV4}$	—	3.2	ns	3
Output hold from local bus clock (except LAD/LDP and LALE)	$t_{LBKHOX1}$	0.9	—	ns	3
Output hold from local bus clock for LAD/LDP	$t_{LBKHOX2}$	0.9	—	ns	3
Local bus clock to output high Impedance (except LAD/LDP and LALE)	$t_{LBKHOZ1}$	—	2.6	ns	5

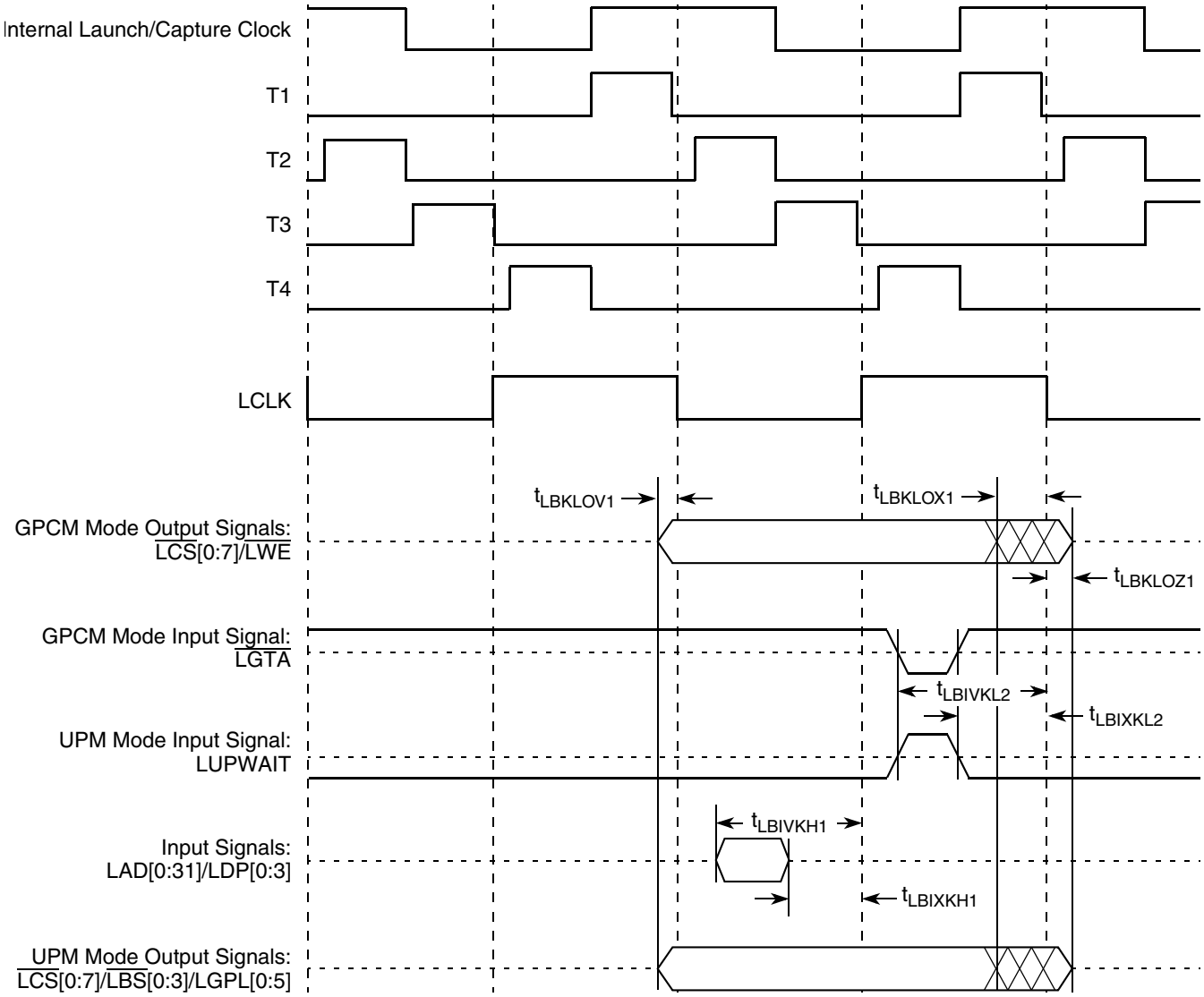

Figure 33. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 8 or 16 (PLL Bypass Mode)

11 Programmable Interrupt Controller

In IRQ edge trigger mode, when an external interrupt signal is asserted (according to the programmed polarity), it must remain the assertion for at least 3 system clocks (SYSCLK periods).

13.2 I²C AC Electrical Specifications

Table 52 provides the AC timing parameters for the I²C interfaces.

Table 52. I²C AC Electrical Specifications

All values refer to V_{IH} (min) and V_{IL} (max) levels (see Table 51).

Parameter	Symbol[1]	Min	Max	Unit	Notes
SCL clock frequency	f_{I2C}	0	400	kHz	—
Low period of the SCL clock	t_{I2CL}	1.3	—	μs	—
High period of the SCL clock	t_{I2CH}	0.6	—	μs	—
Setup time for a repeated START condition	t_{I2SVKH}	0.6	—	μs	—
Hold time (repeated) START condition (after this period, the first clock pulse is generated)	t_{I2SXKL}	0.6	—	μs	—
Data setup time	t_{I2DVKH}	100	—	ns	—
Data hold time: CBUS compatible masters I²C bus devices	t_{I2DXKL}	 — 0	 — —	μs	2
Data output delay time	t_{I2OVKL}	—	0.9		3
Set-up time for STOP condition	t_{I2PVKH}	0.6	—	μs	—
Rise time of both SDA and SCL signals	t_{I2CR}	$20 + 0.1\ C_b$	300	ns	4
Fall time of both SDA and SCL signals	t_{I2CF}	$20 + 0.1\ C_b$	300	ns	4
Bus free time between a STOP and START condition	t_{I2KHDX}	1.3	—	μs	—
Noise margin at the LOW level for each connected device (including hysteresis)	V_{NL}	$0.1 \times OV_{DD}$	—	V	—
Noise margin at the HIGH level for each connected device (including hysteresis)	V_{NH}	$0.2 \times OV_{DD}$	—	V	—

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{I2DVKH} symbolizes I²C timing (I2) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. Also, t_{I2SXKL} symbolizes I²C timing (I2) for the time that the data with respect to the start condition (S) went invalid (X) relative to the t_{I2C} clock reference (K) going to the low (L) state or hold time. Also, t_{I2PVKH} symbolizes I²C timing (I2) for the time that the data with respect to the stop condition (P) reaching the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. The MPC8544E provides a hold time of at least 300 ns for the SDA signal (referred to the V_{IH}min of the SCL signal) to bridge the undefined region of the falling edge of SCL.
3. The maximum t_{I2DXKL} has only to be met if the device does not stretch the LOW period (t_{I2CL}) of the SCL signal.
4. C_B = capacitance of one bus line in pF.

Using this waveform, the definitions are as follows. To simplify illustration, the following definitions assume that the SerDes transmitter and receiver operate in a fully symmetrical differential signaling environment.

1. **Single-Ended Swing**

   The transmitter output signals and the receiver input signals SD*n*_TX, $\overline{\text{SD}n\text{\_TX}}$, SD*n*_RX and $\overline{\text{SD}n\text{\_RX}}$ each have a peak-to-peak swing of A - B Volts. This is also referred as each signal wire's Single-Ended Swing.

2. **Differential Output Voltage, V_{OD}** (or **Differential Output Swing**):

   The Differential Output Voltage (or Swing) of the transmitter, V_{OD}, is defined as the difference of the two complimentary output voltages: $V_{SDn\_TX} - V_{\overline{SDn\_TX}}$. The V_{OD} value can be either positive or negative.

3. **Differential Input Voltage, V_{ID}** (or **Differential Input Swing**):

   The Differential Input Voltage (or Swing) of the receiver, V_{ID}, is defined as the difference of the two complimentary input voltages: $V_{SDn\_RX} - V_{\overline{SDn\_RX}}$. The V_{ID} value can be either positive or negative.

4. **Differential Peak Voltage, V_{DIFFp}**

   The peak value of the differential transmitter output signal or the differential receiver input signal is defined as Differential Peak Voltage, $V_{DIFFp} = |A - B|$ Volts.

5. **Differential Peak-to-Peak, $V_{DIFFp-p}$**

   Since the differential output signal of the transmitter and the differential input signal of the receiver each range from A – B to –(A – B) Volts, the peak-to-peak value of the differential transmitter output signal or the differential receiver input signal is defined as Differential Peak-to-Peak Voltage, $V_{DIFFp-p} = 2*V_{DIFFp} = 2 * |(A - B)|$ Volts, which is twice of differential swing in amplitude, or twice of the differential peak. For example, the output differential peak-peak voltage can also be calculated as $V_{TX-DIFFp-p} = 2*|V_{OD}|$.

6. **Differential Waveform**

   The differential waveform is constructed by subtracting the inverting signal ($\overline{\text{SD}n\text{\_TX}}$, for example) from the non-inverting signal (SD*n*_TX, for example) within a differential pair. There is only one signal trace curve in a differential waveform. The voltage represented in the differential waveform is not referenced to ground. Refer to Figure 44 as an example for differential waveform.

7. **Common Mode Voltage, V_{cm}**

   The Common Mode Voltage is equal to one half of the sum of the voltages between each conductor of a balanced interchange circuit and ground. In this example, for SerDes output, $V_{cm\_out} = V_{SDn\_TX} + V_{\overline{SDn\_TX}} = (A + B) / 2$, which is the arithmetic mean of the two complimentary output voltages within a differential pair. In a system, the common mode voltage may often differ from one component's output to the other's input. Sometimes, it may be even different between the receiver input and driver output circuits within the same component. It is also referred as the DC offset in some occasions.

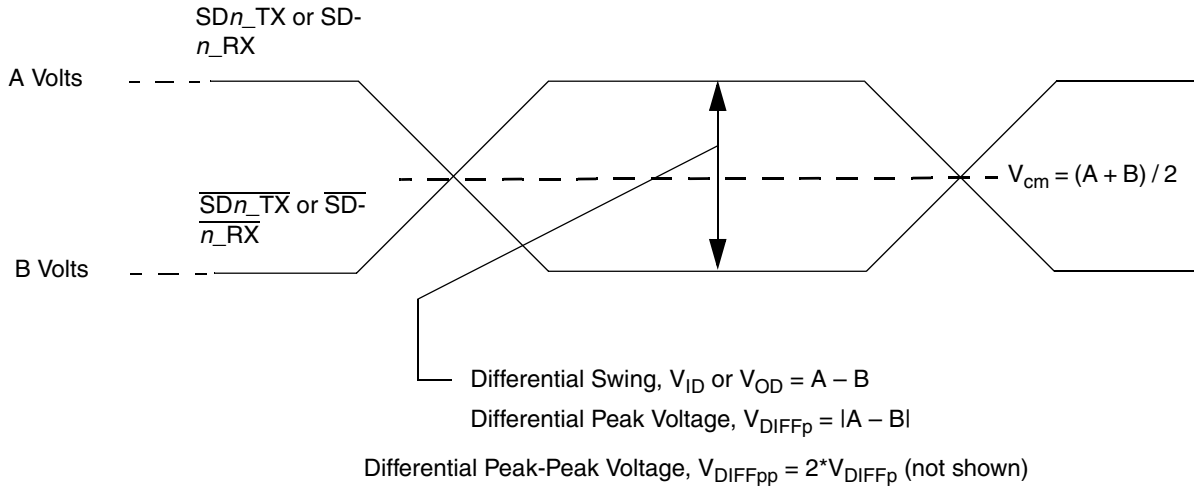

Figure 44. Differential Voltage Definitions for Transmitter or Receiver

To illustrate these definitions using real values, consider the case of a CML (Current Mode Logic) transmitter that has a common mode voltage of 2.25 V and each of its outputs, TD and $\overline{\text{TD}}$, has a swing that goes between 2.5 V and 2.0 V. Using these values, the peak-to-peak voltage swing of each signal (TD or $\overline{\text{TD}}$) is 500 mV p-p, which is referred as the single-ended swing for each signal. In this example, since the differential signaling environment is fully symmetrical, the transmitter output's differential swing (V_{OD}) has the same amplitude as each signal's single-ended swing. The differential output signal ranges between 500 mV and –500 mV, in other words, V_{OD} is 500 mV in one phase and –500 mV in the other phase. The peak differential voltage (V_{DIFFp}) is 500 mV. The peak-to-peak differential voltage ($V_{DIFFp-p}$) is 1000 mV p-p.

16.2 SerDes Reference Clocks

The SerDes reference clock inputs are applied to an internal PLL whose output creates the clock used by the corresponding SerDes lanes. The SerDes reference clocks inputs are SD1_REF_CLK and $\overline{\text{SD1\_REF\_CLK}}$ for PCI Express1, PCI Express2. SD2_REF_CLK, and $\overline{\text{SD2\_REF\_CLK}}$ for the PCI Express3 or SGMII interface, respectively. The following sections describe the SerDes reference clock requirements and some application information.

16.2.1 SerDes Reference Clock Receiver Characteristics

Figure 45 shows a receiver reference diagram of the SerDes reference clocks.

- The supply voltage requirements for XV_{DD_SRDS2} are specified in Table 1 and Table 2.
- SerDes reference clock receiver reference circuit structure
  - The SD*n*_REF_CLK and $\overline{\text{SD}n\text{\_REF\_CLK}}$ are internally AC-coupled differential inputs as shown in Figure 45. Each differential clock input (SD*n*_REF_CLK or $\overline{\text{SD}n\text{\_REF\_CLK}}$) has a 50-Ω termination to SGND_SRDS*n* (xcorevss) followed by on-chip AC-coupling.
  - The external reference clock driver must be able to drive this termination.

Figure 49 shows the SerDes reference clock connection reference circuits for HCSL type clock driver. It assumes that the DC levels of the clock driver chip is compatible with MPC8544E SerDes reference clock input's DC requirement.

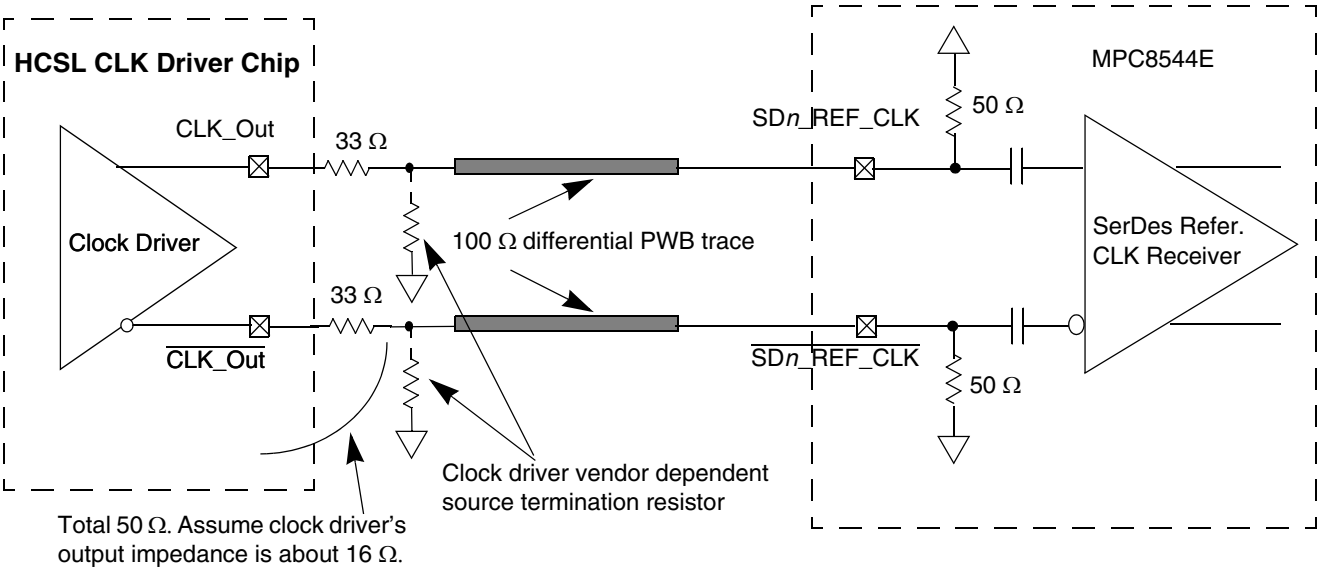

Figure 49. DC-Coupled Differential Connection with HCSL Clock Driver (Reference Only)

Figure 50 shows the SerDes reference clock connection reference circuits for LVDS type clock driver. Since LVDS clock driver's common mode voltage is higher than the MPC8544E SerDes reference clock input's allowed range (100 to 400mV), AC-coupled connection scheme must be used. It assumes the LVDS output driver features 50-Ω termination resistor. It also assumes that the LVDS transmitter establishes its own common mode level without relying on the receiver or other external component.

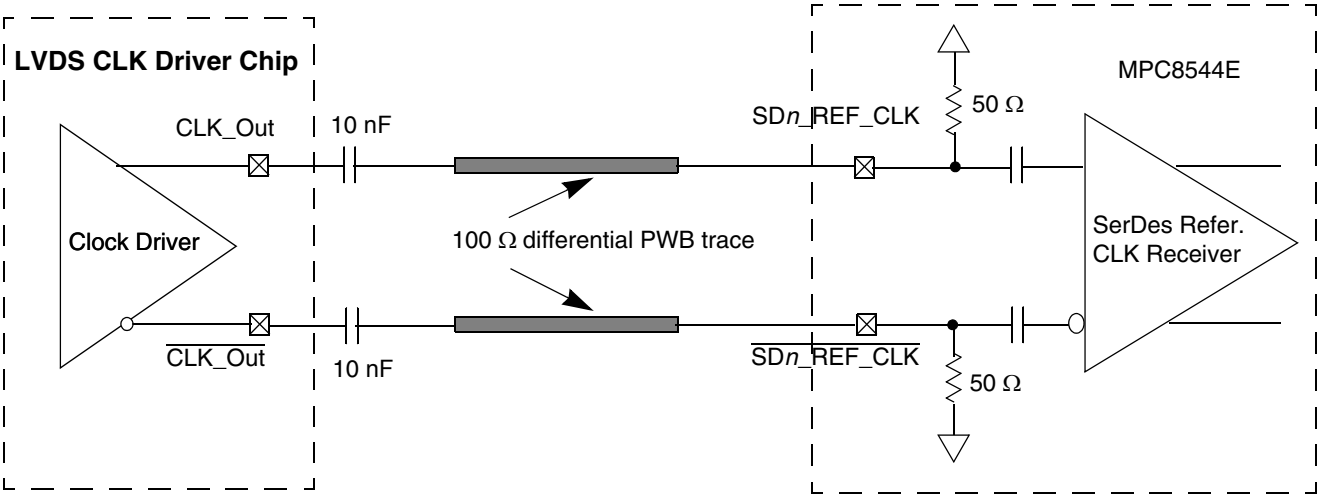

Figure 50. AC-Coupled Differential Connection with LVDS Clock Driver (Reference Only)

Figure 51 shows the SerDes reference clock connection reference circuits for LVPECL type clock driver. Since LVPECL driver's DC levels (both common mode voltages and output swing) are incompatible with MPC8544E SerDes reference clock input's DC requirement, AC-coupling has to be used. Figure 51

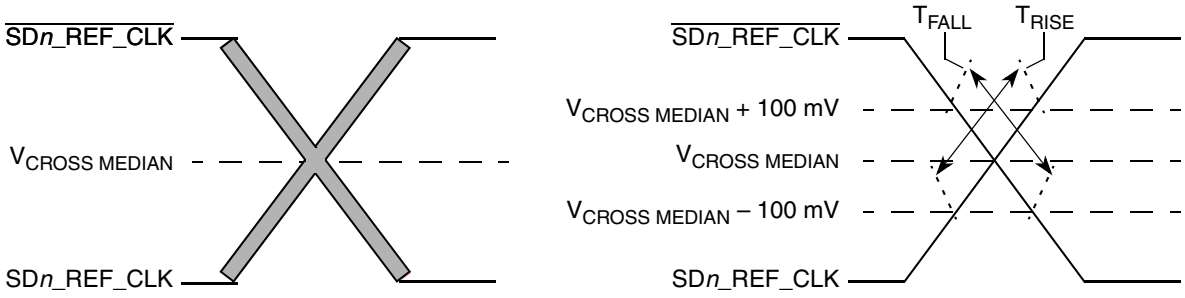

Figure 54. Single-Ended Measurement Points for Rise and Fall Time Matching

The other detailed AC requirements of the SerDes reference clocks is defined by each interface protocol based on application usage. Refer to the following sections for detailed information:

- Section 8.3.1, "The $\overline{\text{DBWO}}$ Signal"
- Section 17.2, "AC Requirements for PCI Express SerDes Clocks"

16.2.4.1 Spread Spectrum Clock

SD1_REF_CLK/$\overline{\text{SD1\_REF\_CLK}}$ were designed to work with a spread spectrum clock (+0 to –0.5% spreading at 30–33 kHz rate is allowed), assuming both ends have same reference clock. For better results, a source without significant unintended modulation should be used.

SD2_REF_CLK/$\overline{\text{SD2\_REF\_CLK}}$ are not intended to be used with, and should not be clocked by, a spread spectrum clock source.

16.3 SerDes Transmitter and Receiver Reference Circuits

Figure 55 shows the reference circuits for SerDes data lane's transmitter and receiver.

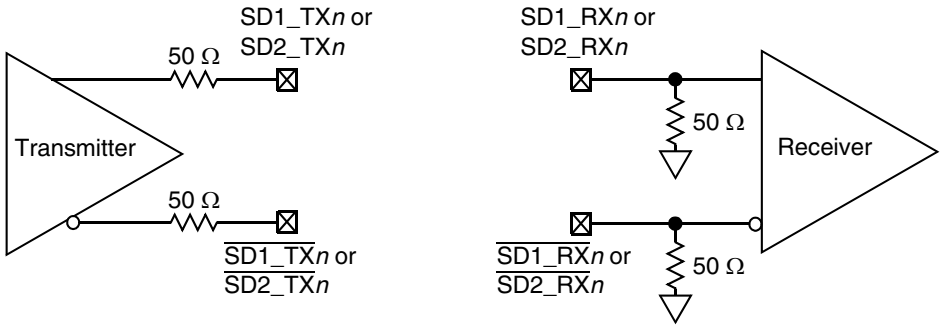

Figure 55. SerDes Transmitter and Receiver Reference Circuits

The DC and AC specification of SerDes data lanes are defined in the section below (PCI Express or SGMII) in this document based on the application usage:

- Section 8.3, "SGMII Interface Electrical Characteristics"
- Section 17, "PCI Express"

Please note that external AC Coupling capacitor is required for the above serial transmission protocols with the capacitor value defined in specification of each protocol section.

17 PCI Express

This section describes the DC and AC electrical specifications for the PCI Express bus of the MPC8544.

17.1 DC Requirements for PCI Express SD_REF_CLK and $\overline{\text{SD\_REF\_CLK}}$

For more information, see Section 16.2, "SerDes Reference Clocks."

17.2 AC Requirements for PCI Express SerDes Clocks

Table 58 provides the AC requirements for the PCI Express SerDes clocks.

Table 58. SD_REF_CLK and $\overline{\text{SD\_REF\_CLK}}$ AC Requirements

Symbol[2]	Parameter Description	Min	Typ	Max	Units	Notes
t_{REF}	REFCLK cycle time	—	10	—	ns	1
t_{REFCJ}	REFCLK cycle-to-cycle jitter. Difference in the period of any two adjacent REFCLK cycles	—	—	100	ps	—
t_{REFPJ}	Phase jitter. Deviation in edge location with respect to mean edge location	–50	—	50	ps	—

Notes:
1. Typical based on *PCI Express Specification 2.0*.
2. Guaranteed by characterization.

17.3 Clocking Dependencies

The ports on the two ends of a link must transmit data at a rate that is within 600 parts per million (ppm) of each other at all times. This is specified to allow bit rate clock sources with a ±300 ppm tolerance.

17.4 Physical Layer Specifications

The following is a summary of the specifications for the physical layer of PCI Express on this device. For further details as well as the specifications of the transport and data link layer please refer to the *PCI Express Base Specification*. *Rev. 1.0a*.

Table 59. Differential Transmitter (TX) Output Specifications (continued)

Symbol	Parameter	Min	Nom	Max	Unit	Comments
$T_{crosslink}$	Crosslink random timeout	0	—	1	ms	This random timeout helps resolve conflicts in crosslink configuration by eventually resulting in only one downstream and one upstream port. See Note 7.

Notes:
1. No test load is necessarily associated with this value.
2. Specified at the measurement point into a timing and voltage compliance test load as shown in Figure 58 and measured over any 250 consecutive TX UIs. (Also refer to the transmitter compliance eye diagram shown in Figure 56.)
3. A T_{TX-EYE} = 0.70 UI provides for a total sum of deterministic and random jitter budget of $T_{TX-JITTER-MAX}$ = 0.30 UI for the transmitter collected over any 250 consecutive TX UIs. The $T_{TX-EYE-MEDIAN-to-MAX-JITTER}$ median is less than half of the total TX jitter budget collected over any 250 consecutive TX UIs. It should be noted that the median is not the same as the mean. The jitter median describes the point in time where the number of jitter points on either side is approximately equal as opposed to the averaged time value.
4. The transmitter input impedance shall result in a differential return loss greater than or equal to 12 dB and a common mode return loss greater than or equal to 6 dB over a frequency range of 50 MHz to 1.25 GHz. This input impedance requirement applies to all valid input levels. The reference impedance for return loss measurements is 50 Ω to ground for both the D+ and D– line (that is, as measured by a vector network analyzer with 50-Ω probes—see Figure 58.) Note that the series capacitors C_{TX} is optional for the return loss measurement.
5. Measured between 20%–80% at transmitter package pins into a test load as shown in Figure 58 for both V_{TX-D+} and V_{TX-D-}.
6. See Section 4.3.1.8 of the *PCI Express Base Specifications, Rev 1.0a.*
7. See Section 4.2.6.3 of the *PCI Express Base Specifications, Rev 1.0a.*

17.4.2 Transmitter Compliance Eye Diagrams

The TX eye diagram in Figure 56 is specified using the passive compliance/test measurement load (see Figure 58) in place of any real PCI Express interconnect +RX component.

There are two eye diagrams that must be met for the transmitter. Both eye diagrams must be aligned in time using the jitter median to locate the center of the eye diagram. The different eye diagrams will differ in voltage depending whether it is a transition bit or a de-emphasized bit. The exact reduced voltage level of the de-emphasized bit will always be relative to the transition bit.

The eye diagram must be valid for any 250 consecutive UIs.

A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. The eye diagram is created using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI.

NOTE

It is recommended that the recovered TX UI is calculated using all edges in the 3500 consecutive UI interval with a fit algorithm using a minimization merit function (that is, least squares and median deviation fits).

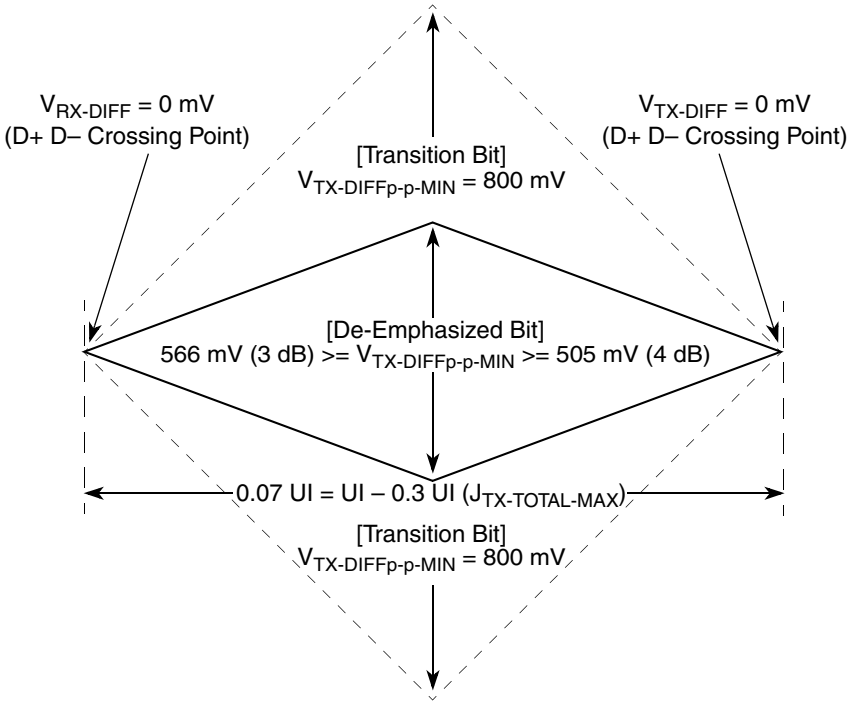

Figure 56. Minimum Transmitter Timing and Voltage Output Compliance Specifications

17.4.3 Differential Receiver (RX) Input Specifications

Table 60 defines the specifications for the differential input at all receivers. The parameters are specified at the component pins.

Table 60. Differential Receiver (RX) Input Specifications

Symbol	Parameter	Min	Nom	Max	Units	Comments
UI	Unit interval	399.88	400	400.12	ps	Each UI is 400 ps ± 300 ppm. UI does not account for spread spectrum clock dictated variations. See Note 1.
$V_{RX-DIFFp-p}$	Differential peak-to-peak input voltage	0.175	—	1.200	V	$V_{RX-DIFFp-p} = 2 \times \lvert V_{RX-D+} - V_{RX-D-} \rvert$ See Note 2.
T_{RX-EYE}	Minimum receiver eye width	0.4	—	—	UI	The maximum interconnect media and transmitter jitter that can be tolerated by the receiver can be derived as $T_{RX-MAX-JITTER} = 1 - T_{RX-EYE} = 0.6$ UI. See Notes 2 and 3.

18 Package Description

This section details package parameters, pin assignments, and dimensions.

18.1 Package Parameters for the MPC8544E FC-PBGA

The package parameters for flip chip plastic ball grid array (FC-PBGA) are provided in Table 61.

Table 61. Package Parameters

Parameter	PBGA[1]
Package outline	29 mm × 29 mm
Interconnects	783
Ball pitch	1 mm
Ball diameter (typical)	0.6 mm
Solder ball (Pb-free)	96.5% Sn 3.5% Ag

Note:
1. (FC-PBGA) without a lid.

Table 62. MPC8544E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
DDR SDRAM Memory Interface				
MDQ[0:63]	A26, B26, C22, D21, D25, B25, D22, E21, A24, A23, B20, A20, A25, B24, B21, A21, E19, D19, E16, C16, F19, F18, F17, D16, B18, A18, A15, B14, B19, A19, A16, B15, D1, F3, G1, H2, E4, G5, H3, J4, B2, C3, F2, G2, A2, B3, E1, F1, L5, L4,N3, P3, J3, K4, N4, P4, J1, K1, P1, R1, J2, K2, N1, R2	I/O	GV_{DD}	—
MECC[0:7]	G12, D14, F11, C11, G14, F14,C13, D12	I/O	GV_{DD}	—
MDM[0:8]	C25, B23, D18, B17, G4, C2, L3, L2, F13	O	GV_{DD}	21
$\overline{\text{MDQS}}$[0:8]	D24, B22, C18, A17, J5, C1, M4, M2, E13	I/O	GV_{DD}	—
MDQS[0:8]	C23, A22, E17, B16, K5, D2, M3, P2, D13	I/O	GV_{DD}	—
MA[0:15]	B7, G8, C8, A10, D9, C10, A11, F9, E9, B12, A5, A12, D11, F7, E10, F10	O	GV_{DD}	—
MBA[0:2]	A4, B5, B13	O	GV_{DD}	—
$\overline{\text{MWE}}$	B4	O	GV_{DD}	—
$\overline{\text{MCAS}}$	E7	O	GV_{DD}	—
$\overline{\text{MRAS}}$	C5	O	GV_{DD}	—
MCKE[0:3]	H10, K10, G10, H9	O	GV_{DD}	10
$\overline{\text{MCS}}$[0:3]	D3, H6, C4, G6	O	GV_{DD}	—
MCK[0:5]	A9, J11, J6, A8, J13, H8	O	GV_{DD}	—
$\overline{\text{MCK}}$[0:5]	B9, H11, K6, B8, H13, J8	O	GV_{DD}	—
MODT[0:3]	E5, H7, E6, F6	O	GV_{DD}	—
MDIC[0:1]	H15, K15	I/O	GV_{DD}	25
TEST_IN	A13	I	—	27
TEST_OUT	A6	O	—	17
Local Bus Controller Interface				
LAD[0:31]	K22, L21, L22, K23, K24, L24, L25, K25, L28, L27, K28, K27, J28, H28, H27, G27, G26, F28, F26, F25, E28, E27, E26, F24, E24, C26, G24, E23, G23, F22, G22, G21	I/O	BV_{DD}	23
LDP[0:3]	K26, G28, B27, E25	I/O	BV_{DD}	
LA[27]	L19	O	BV_{DD}	4, 8
LA[28:31]	K16, K17, H17,G17	O	BV_{DD}	4, 6, 8
$\overline{\text{LCS}}$[0:4]	K18, G19, H19, H20, G16	O	BV_{DD}	—
$\overline{\text{LCS5}}$/$\overline{\text{DMA\_DREQ2}}$	H16	I/O	BV_{DD}	1

Table 62. MPC8544E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
$\overline{\text{SD2\_REF\_CLK}}$	AF2	I	XV_{DD}	—
SD2_TST_CLK	AG4	—	—	—
$\overline{\text{SD2\_TST\_CLK}}$	AF4	—	—	—
General-Purpose Output				
GPOUT[0:7]	AF22, AH23, AG27, AH25, AF21, AF25, AG26, AF26	O	OV_{DD}	—
General-Purpose Input				
GPIN[0:7]	AH24, AG24, AD23, AE21, AD22, AF23, AG25, AE20	I	OV_{DD}	—
System Control				
$\overline{\text{HRESET}}$	AG16	I	OV_{DD}	—
$\overline{\text{HRESET\_REQ}}$	AG15	O	OV_{DD}	21
$\overline{\text{SRESET}}$	AG19	I	OV_{DD}	—
$\overline{\text{CKSTP\_IN}}$	AH5	I	OV_{DD}	—
$\overline{\text{CKSTP\_OUT}}$	AA12	O	OV_{DD}	2, 4
Debug				
TRIG_IN	AC5	I	OV_{DD}	—
TRIG_OUT/READY/ $\overline{\text{QUIESCE}}$	AB5	O	OV_{DD}	5, 8, 15, 21
MSRCID[0:1]	Y7, W9	O	OV_{DD}	4, 5, 8
MSRCID[2:4]	AA9, AB6, AD5	O	OV_{DD}	5, 15, 21
MDVAL	Y8	O	OV_{DD}	5
CLK_OUT	AE16	O	OV_{DD}	10
Clock				
RTC	AF15	I	OV_{DD}	—
SYSCLK	AH16	I	OV_{DD}	—
JTAG				
TCK	AG28	I	OV_{DD}	—
TDI	AH28	I	OV_{DD}	11
TDO	AF28	O	OV_{DD}	10
TMS	AH27	I	OV_{DD}	11
$\overline{\text{TRST}}$	AH22	I	OV_{DD}	11

Table 71 provides the thermal resistance with heat sink in open flow.

Table 71. Thermal Resistance with Heat Sink in Open Flow

Heat Sink with Thermal Grease	Air Flow	Thermal Resistance (°C/W)
Wakefield 53 × 53 × 25 mm pin fin	Natural convection	6.1
Wakefield 53 × 53 × 25 mm pin fin	1 m/s	3.0
Aavid 35 × 31 × 23 mm pin fin	Natural convection	8.1
Aavid 35 × 31 × 23 mm pin fin	1 m/s	4.3
Aavid 30 × 30 × 9.4 mm pin fin	Natural convection	11.6
Aavid 30 × 30 × 9.4 mm pin fin	1 m/s	6.7
Aavid 43 × 41 × 16.5 mm pin fin	Natural convection	8.3
Aavid 43 × 41 × 16.5 mm pin fin	1 m/s	4.3

Simulations with heat sinks were done with the package mounted on the 2s2p thermal test board. The thermal interface material was a typical thermal grease such as Dow Corning 340 or Wakefield 120 grease. For system thermal modeling, the MPC8544E thermal model without a lid is shown in Figure 60. The substrate is modeled as a block 29 × 29 × 1.18 mm with an in-plane conductivity of 18.0 W/m•K and a through-plane conductivity of 1.0 W/m•K. The solder balls and air are modeled as a single block 29 × 29 × 0.58 mm with an in-plane conductivity of 0.034 W/m•K and a through plane conductivity of 12.1 W/m•K. The die is modeled as 7.6 × 8.4 mm with a thickness of 0.75 mm. The bump/underfill layer is modeled as a collapsed thermal resistance between the die and substrate assuming a conductivity of 6.5 W/m•K in the thickness dimension of 0.07 mm. The die is centered on the substrate. The thermal model uses approximate dimensions to reduce grid. Please refer to Figure 59 for actual dimensions.

20.2 Recommended Thermal Model

Table 72 shows the MPC8544E thermal model.

Table 72. MPC8544EThermal Model

Conductivity	Value	Units
Die (7.6 × 8.4 × 0.75mm)		
Silicon	Temperature dependent	—
Bump/Underfill (7.6 × 8.4 × 0.070 mm) Collapsed Thermal Resistance		
Kz	6.5	W/m•K
Substrate (29 × 29 × 1.18 mm)		
Kx	18	W/m•K
Ky	18	
Kz	1.0	

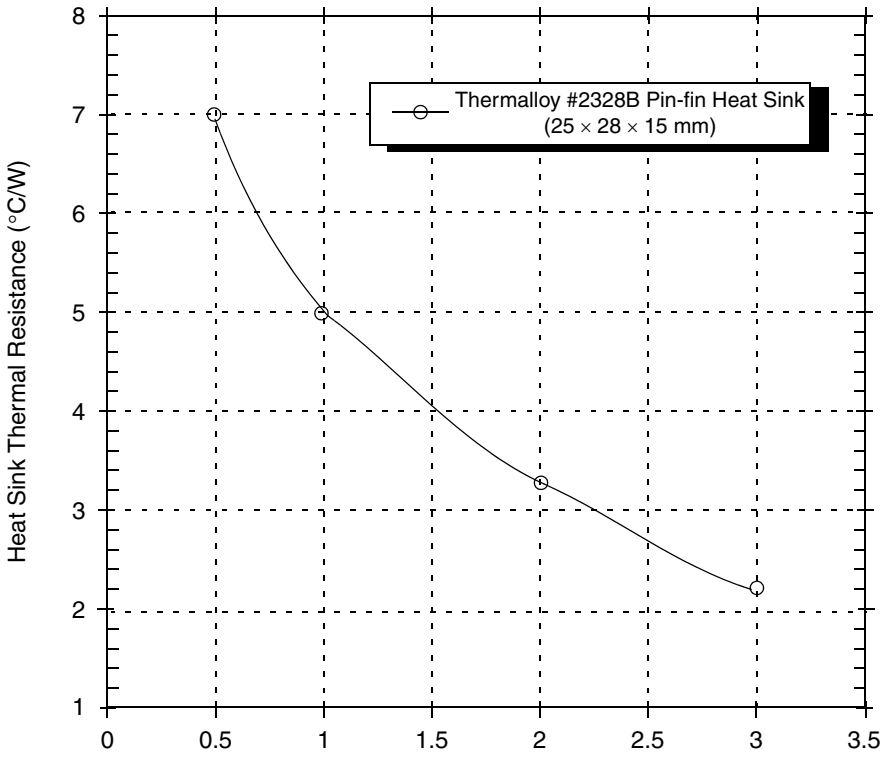

Figure 64. Approach Air Velocity (m/s)

20.3.4 Temperature Diode

The MPC8544E has a temperature diode on the microprocessor that can be used in conjunction with other system temperature monitoring devices (such as Analog Devices, ADT7461™). These devices use the negative temperature coefficient of a diode operated at a constant current to determine the temperature of the microprocessor and its environment. It is recommended that each device be individually calibrated.

The following are voltage forward biased range of the on-board temperature diode:

$V_f > 0.40$ V

$V_f < 0.90$ V

An approximate value of the ideality may be obtained by calibrating the device near the expected operating temperature. The ideality factor is defined as the deviation from the ideal diode equation:

$$I_{fw} = \mathbf{I_s}\left[e^{\frac{qV_f}{nKT}} - \mathbf{1}\right]$$

Another useful equation is:

$$\mathbf{V_H - V_L = n}\frac{KT}{q}\left[\boldsymbol{ln}\ \frac{I_H}{I_L}\right]$$